NSN 5961-01-101-7899

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Inclosure Material:

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Metal
Overall Length:
Between 0.250 inches and 0.450 inches
Terminal Length:
Between 0.312 inches and 0.500 inches
Overall Diameter:
0.875 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Collector
Internal Junction Configuration:
Npn
Mounting Method:
Terminal and threaded stud
Terminal Circle Diameter:
0.430 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
650.0 breakdown voltage, collector-to-base, emitter open and 400.0 breakdown voltage, collector-to-emitter, base open and 7.0
breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
Between 5.00 amperes source cutoff current and 15.00 amperes source cutoff current
Power Rating Per Characteristic:
175.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Terminal Type And Quantity:
1 case and 2 pin
Specification Data:
80131-release6732 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

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